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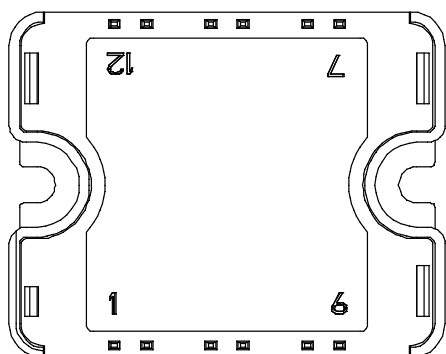
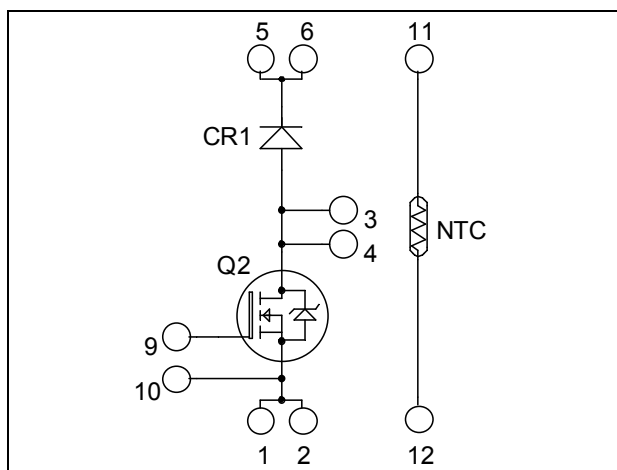


Boost chopper MOSFET Power Module

$V_{DSS} = 1000V$

$R_{DSon} = 330m\Omega$ typ @ $T_j = 25^\circ C$

$I_D = 23A$ @ $T_c = 25^\circ C$



Pins 1/2 ; 3/4 ; 5/6 must be shorted together

Application

- AC and DC motor control
- Switched Mode Power Supplies
- Power Factor Correction

Features

- Power MOS 8™ MOSFETs
 - Low R_{DSon}
 - Low input and Miller capacitance
 - Low gate charge
 - Avalanche energy rated
 - Very rugged
- Very low stray inductance
- Internal thermistor for temperature monitoring
- High level of integration

Benefits

- Outstanding performance at high frequency operation
- Direct mounting to heatsink (isolated package)
- Low junction to case thermal resistance
- Solderable terminals both for power and signal for easy PCB mounting
- Low profile
- RoHS Compliant

Absolute maximum ratings

Symbol	Parameter	Max ratings	Unit
V_{DSS}	Drain - Source Breakdown Voltage	1000	V
I_D	Continuous Drain Current	$T_c = 25^\circ C$	23
		$T_c = 80^\circ C$	17
I_{DM}	Pulsed Drain current	140	A
V_{GS}	Gate - Source Voltage	± 30	V
R_{DSon}	Drain - Source ON Resistance	396	mΩ
P_D	Maximum Power Dissipation	$T_c = 25^\circ C$	390
I_{AR}	Avalanche current (repetitive and non repetitive)	18	W
			A

CAUTION: These Devices are sensitive to Electrostatic Discharge. Proper Handling Procedures Should Be Followed. See application note APT0502 on www.microsemi.com

All ratings @ $T_j = 25^\circ\text{C}$ unless otherwise specified

Electrical Characteristics

Symbol	Characteristic	Test Conditions	Min	Typ	Max	Unit
I_{DSS}	Zero Gate Voltage Drain Current	$V_{DS} = 1000\text{V}$ $V_{GS} = 0\text{V}$			100	μA
		$T_j = 125^\circ\text{C}$			500	
$R_{DS(on)}$	Drain – Source on Resistance	$V_{GS} = 10\text{V}$, $I_D = 18\text{A}$		330	396	$\text{m}\Omega$
$V_{GS(th)}$	Gate Threshold Voltage	$V_{GS} = V_{DS}$, $I_D = 2.5\text{mA}$	3	4	5	V
I_{GSS}	Gate – Source Leakage Current	$V_{GS} = \pm 30\text{V}$			± 100	nA

Dynamic Characteristics

Symbol	Characteristic	Test Conditions	Min	Typ	Max	Unit
C_{iss}	Input Capacitance	$V_{GS} = 0\text{V}$		7868		pF
C_{oss}	Output Capacitance	$V_{DS} = 25\text{V}$		825		
C_{rss}	Reverse Transfer Capacitance	$f = 1\text{MHz}$		104		
Q_g	Total gate Charge	$V_{GS} = 10\text{V}$		305		nC
Q_{gs}	Gate – Source Charge	$V_{Bus} = 500\text{V}$		55		
Q_{gd}	Gate – Drain Charge	$I_D = 18\text{A}$		145		
$T_{d(on)}$	Turn-on Delay Time	Resistive switching @ 25°C $V_{GS} = 15\text{V}$ $V_{Bus} = 667\text{V}$ $I_D = 18\text{A}$ $R_G = 2.2\Omega$		44		ns
T_r	Rise Time			40		
$T_{d(off)}$	Turn-off Delay Time			150		
T_f	Fall Time			38		

Chopper diode ratings and characteristics

Symbol	Characteristic	Test Conditions	Min	Typ	Max	Unit
V_{RRM}	Maximum Peak Repetitive Reverse Voltage		1200			V
I_{RM}	Maximum Reverse Leakage Current	$V_R = 1200\text{V}$			100	μA
		$T_j = 125^\circ\text{C}$			500	
I_F	DC Forward Current	$T_c = 80^\circ\text{C}$		30		A
V_F	Diode Forward Voltage	$I_F = 30\text{A}$		2.6	3.1	V
		$I_F = 60\text{A}$		3.2		
		$I_F = 30\text{A}$, $T_j = 125^\circ\text{C}$		1.8		
t_{rr}	Reverse Recovery Time	$I_F = 30\text{A}$, $T_j = 25^\circ\text{C}$		300		ns
		$T_j = 125^\circ\text{C}$		380		
Q_{rr}	Reverse Recovery Charge	$V_R = 800\text{V}$, $di/dt = 200\text{A}/\mu\text{s}$, $T_j = 25^\circ\text{C}$		360		nC
		$T_j = 125^\circ\text{C}$		1700		

Thermal and package characteristics

Symbol	Characteristic			Min	Typ	Max	Unit
R _{thJC}	Junction to Case Thermal Resistance		Transistor			0.32	°C/W
			Diode			1.2	
V _{ISOL}	RMS Isolation Voltage, any terminal to case t =1 min, 50/60Hz			4000			V
T _J	Operating junction temperature range			-40		150	°C
T _{STG}	Storage Temperature Range			-40		125	
T _C	Operating Case Temperature			-40		100	
Torque	Mounting torque	To heatsink	M4	2		3	N.m
Wt	Package Weight					80	g



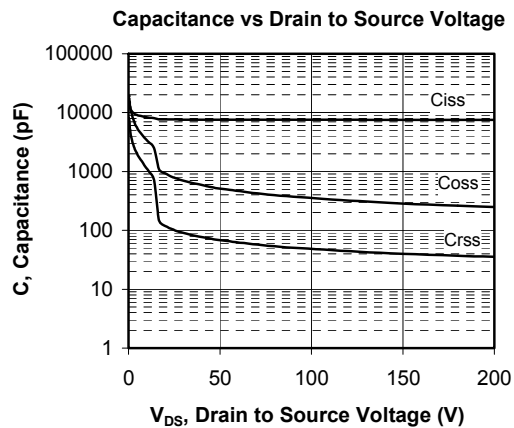
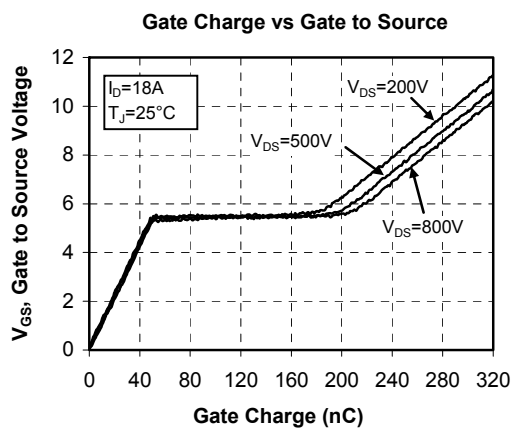
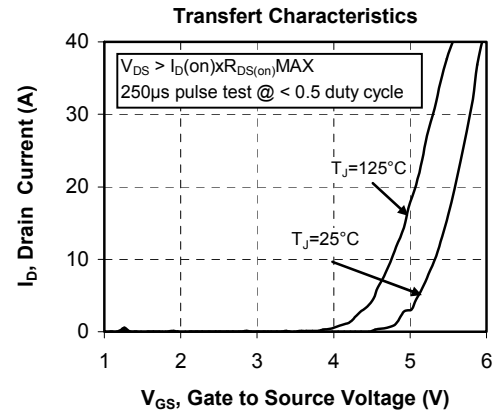
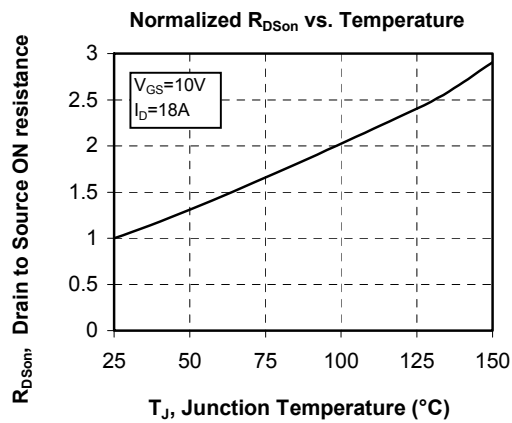
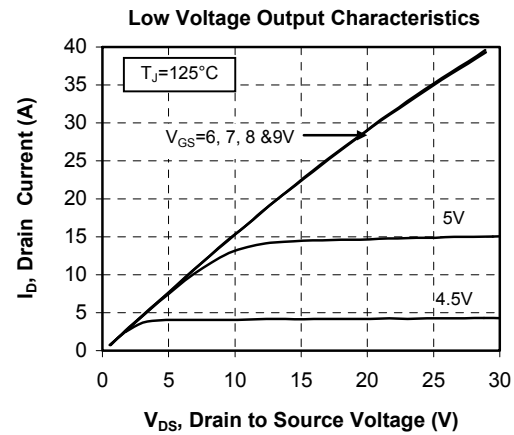
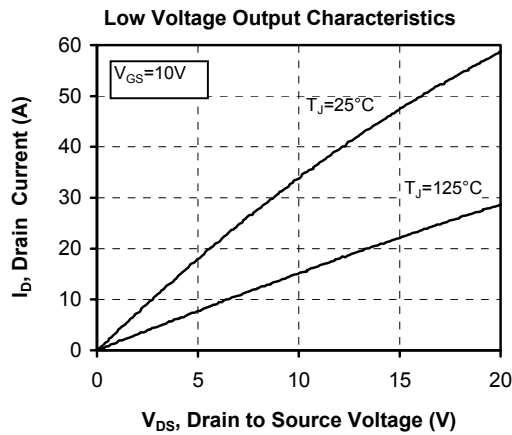
<i>Symbol</i>	<i>Characteristic</i>	<i>Min</i>	<i>Typ</i>	<i>Max</i>	<i>Unit</i>
R ₂₅	Resistance @ 25°C		50		kΩ
B _{25/85}	T ₂₅ = 298.15 K		3952		K

$$R_T = \frac{R_{25}}{\exp \left[B_{25/85} \left(\frac{1}{T_{25}} - \frac{1}{T} \right) \right]}$$

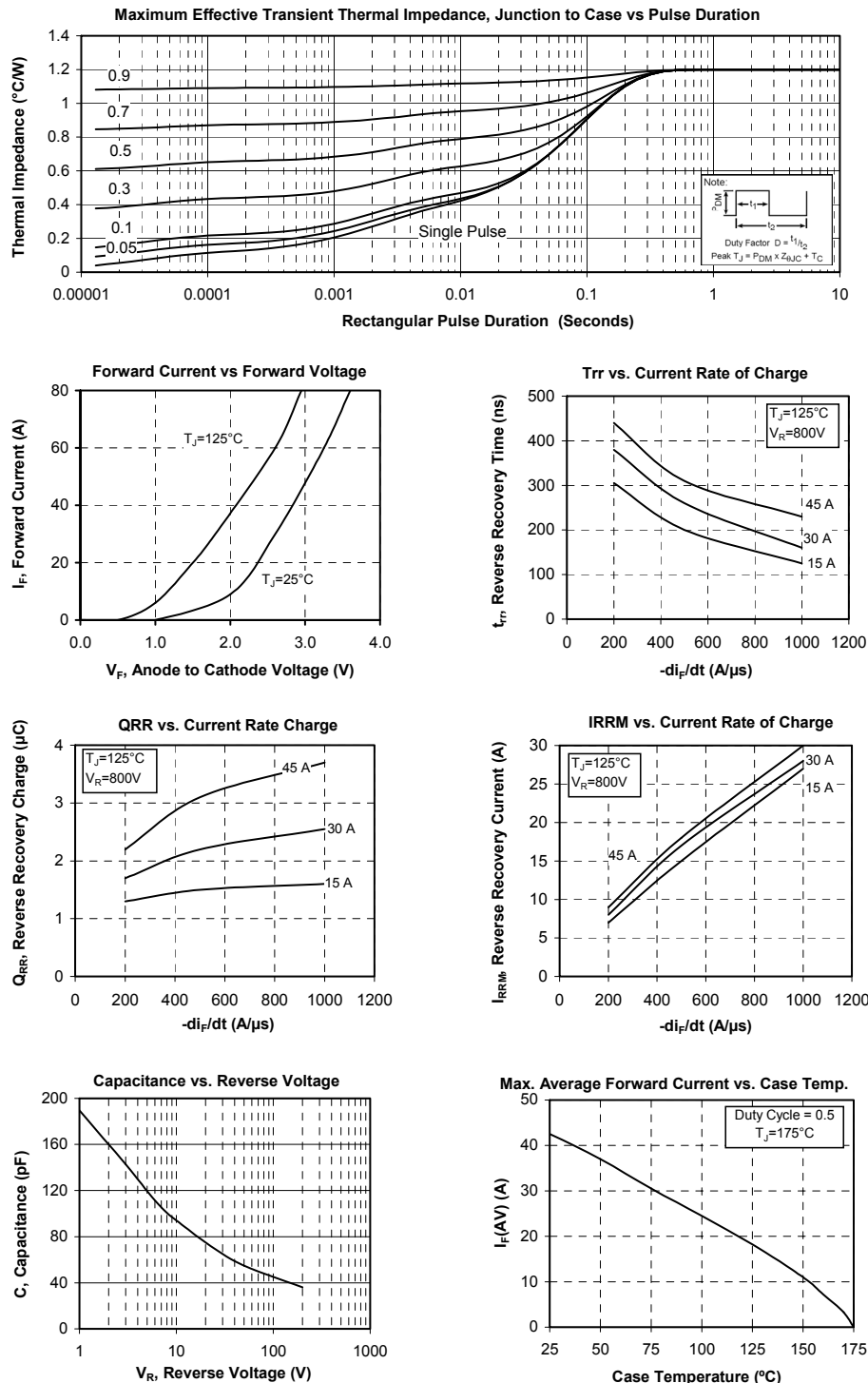
T: Thermistor temperature
R_T: Thermistor value at T

Typical Mosfet Performance Curve

This graph shows the thermal impedance of a single pulse as a function of pulse duration. The y-axis represents Thermal Impedance in °C/W, ranging from 0 to 0.35. The x-axis represents rectangular pulse duration in seconds on a logarithmic scale, ranging from 0.00001 to 10. Multiple curves are plotted for different duty factors (0.05, 0.1, 0.3, 0.5, 0.7, 0.9). As the pulse duration increases, the thermal impedance for all duty factors converges to a value of approximately 0.32 °C/W. A note in the bottom right corner defines the pulse parameters: P_{DM} is the peak power, t_1 is the pulse width, t_2 is the period, $D = t_1/t_2$ is the duty factor, and the peak junction temperature is given by $T_{J, peak} = P_{DM} \times Z_{\theta JC} + T_C$.



Typical Diode Performance Curve



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